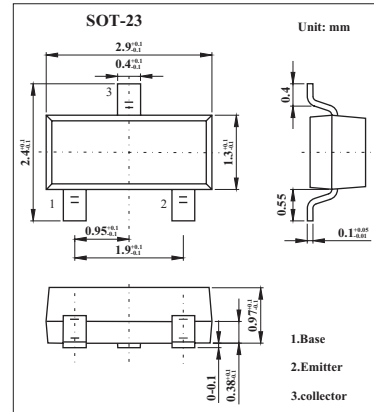


■ Features

- Complementary to KST9014



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _c	-0.1	A
Collector Power Dissipation	P _c	0.2	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =-100uA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _c =-1mA, I _B =0	-45			V
Emitter-base Breakdown voltage	V _{EB0}	I _E =-100uA, I _c =0	-5			V
Collector cutoff current	I _{cBO}	V _{CB} =-50V, I _E =0			-0.1	μ A
Emitter cutoff current	I _{EBO}	V _{EB} =-5V, I _c =0			-0.1	μ A
DC current gain	h _{FE}	V _{CE} =-5V, I _c =-1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-100mA, I _B =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _c =-10mA, f=30MHZ	150			MHz

■ hFE Classification

Marking	M6	
Rank	L	H
hFE	200 to 450	450 to 1000

■ Typical Characteristics

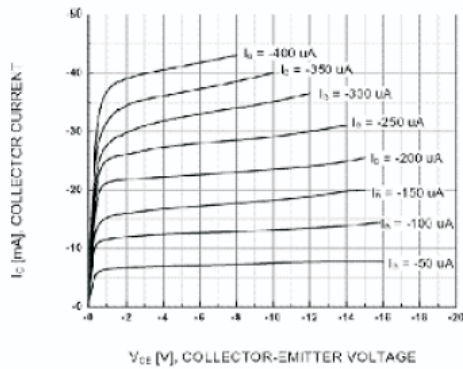


Figure 1. Static Characteristic

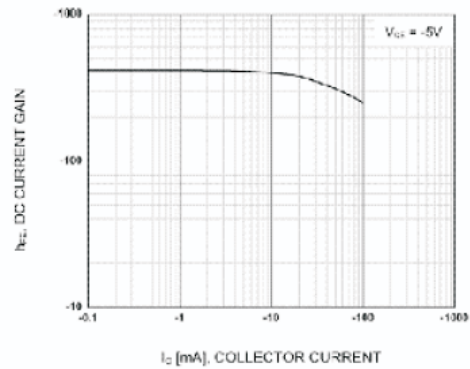


Figure 2. DC current Gain

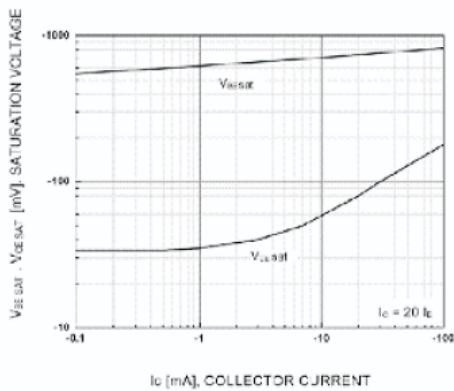


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

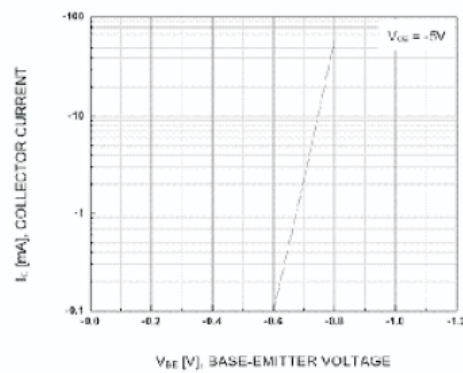


Figure 4. Base-Emitter On Voltage

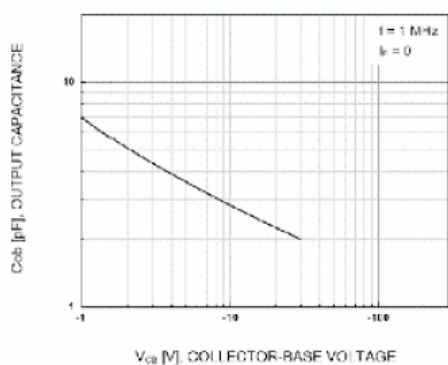


Figure 5. Collector Output Capacitance

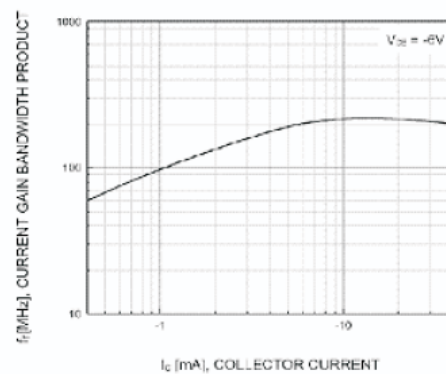


Figure 6. Current Gain Bandwidth Product